

IRFPS29N60LPbF

HEXFET® Power MOSFET

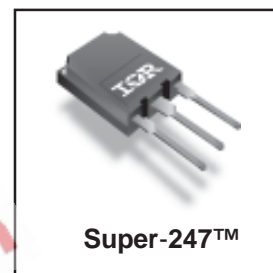
Applications

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control applications
- Lead-Free

V_{DS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
600V	175m Ω	130ns	29A

Features and Benefits

- SuperFast body diode eliminates the need for external diodes in ZVS applications.
- Lower Gate charge results in simpler drive requirements.
- Enhanced dv/dt capabilities offer improved ruggedness.
- Higher Gate voltage threshold offers improved noise immunity.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	29	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	18	
I_{DM}	Pulsed Drain Current ①	110	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	480	W
	Linear Derating Factor	3.8	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	15	V/ns
T_J	Operating Junction and	-55 to + 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	1.1(10)	N•m (lb•in)

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	29	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	110		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}$, $I_S = 29\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	130	190	ns	$T_J = 25^\circ\text{C}$, $I_F = 29\text{A}$
		—	240	360		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	630	950	nC	$T_J = 25^\circ\text{C}$, $I_S = 29\text{A}$, $V_{GS} = 0\text{V}$ ④
		—	1820	2720		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
I_{RRM}	Reverse Recovery Current	—	9.4	14	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

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International
 Rectifier

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	600	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	—	0.53	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	175	210	mΩ	V _{GS} = 10V, I _D = 17A ④
V _{GS(th)}	Gate Threshold Voltage	3.0	—	5.0	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source Leakage Current	—	—	50	μA	V _{DS} = 600V, V _{GS} = 0V
		—	—	2.0	mA	V _{DS} = 480V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100	nA	V _{GS} = -30V
R _G	Internal Gate Resistance	—	0.86	—	Ω	f = 1MHz, open drain

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g _{fs}	Forward Transconductance	15	—	—	S	V _{DS} = 50V, I _D = 17A
Q _g	Total Gate Charge	—	—	220	nC	I _D = 29A
Q _{gs}	Gate-to-Source Charge	—	—	67	nC	V _{DS} = 480V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	96	nC	V _{GS} = 10V, See Fig. 7 & 15 ④
t _{d(on)}	Turn-On Delay Time	—	34	—	ns	V _{DD} = 300V
t _r	Rise Time	—	100	—		I _D = 29A
t _{d(off)}	Turn-Off Delay Time	—	66	—		R _G = 4.3Ω
t _f	Fall Time	—	54	—		V _{GS} = 10V, See Fig. 11a & 11b ④
C _{iss}	Input Capacitance	—	6160	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	530	—		V _{DS} = 25V
C _{riss}	Reverse Transfer Capacitance	—	44	—		f = 1.0MHz, See Fig. 5
C _{oss eff.}	Effective Output Capacitance	—	250	—		V _{GS} = 0V, V _{DS} = 0V to 480V ⑤
C _{oss eff. (ER)}	Effective Output Capacitance (Energy Related)	—	190	—		

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E _{AS}	Single Pulse Avalanche Energy ②	—	570	mJ
I _{AR}	Avalanche Current ①	—	29	A
E _{AR}	Repetitive Avalanche Energy ①	—	48	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑥	—	0.26	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.24	—	
R _{θJA}	Junction-to-Ambient ⑥	—	40	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting T_J = 25°C, L = 1.5mH, R_G = 25Ω, I_{AS} = 29A. (See Figure 12a)
- ③ I_{SD} ≤ 29A, di/dt ≤ 830A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C.

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ C_{oss eff.} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}. C_{oss eff.(ER)} is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑥ R_θ is measured at T_J approximately 90°C

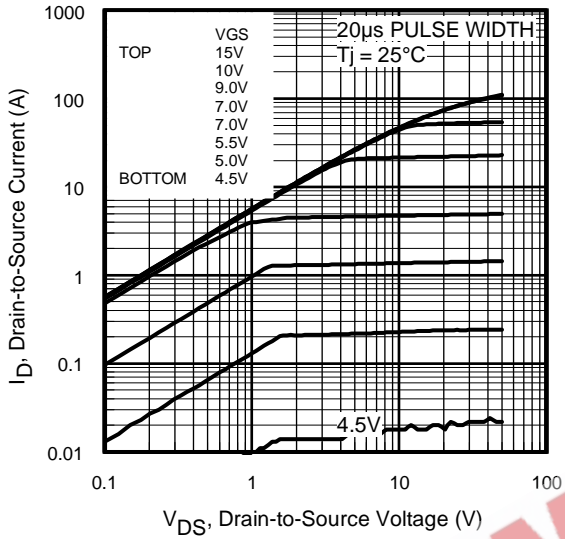


Fig 1. Typical Output Characteristics

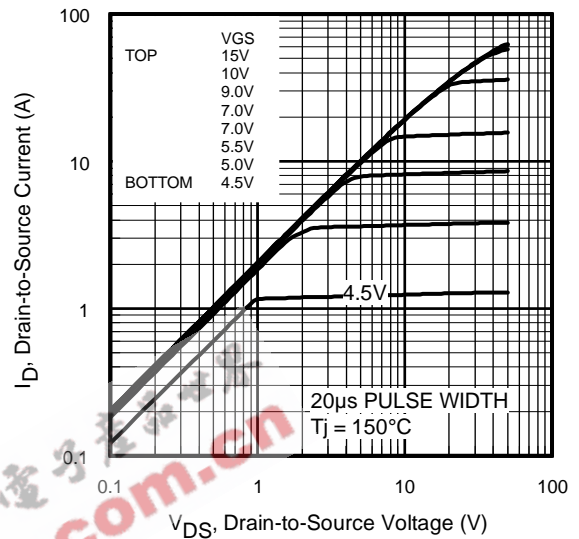


Fig 2. Typical Output Characteristics

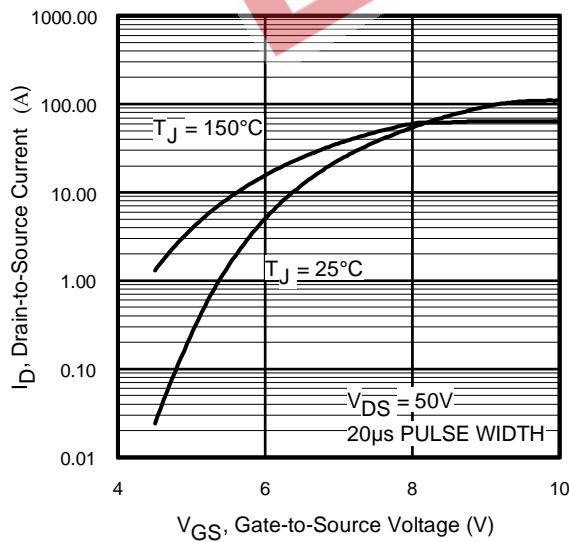


Fig 3. Typical Transfer Characteristics

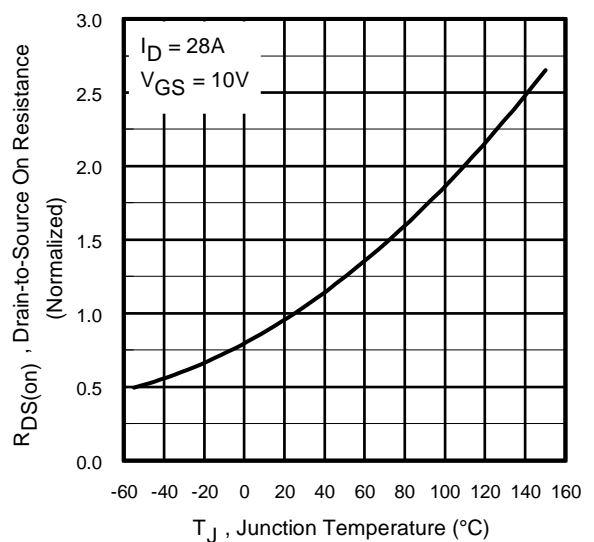


Fig 4. Normalized On-Resistance vs. Temperature

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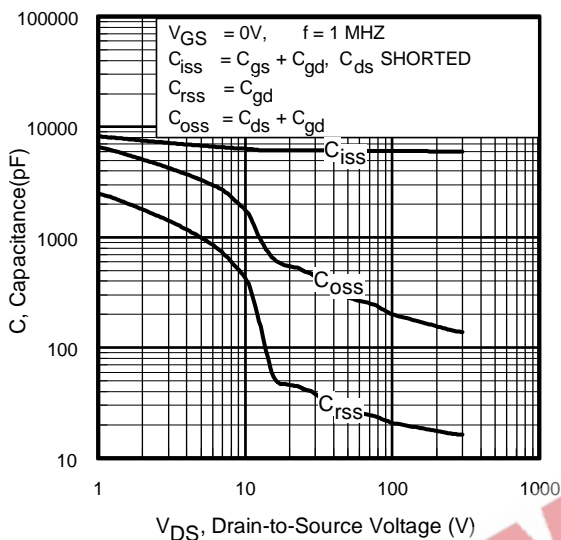


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

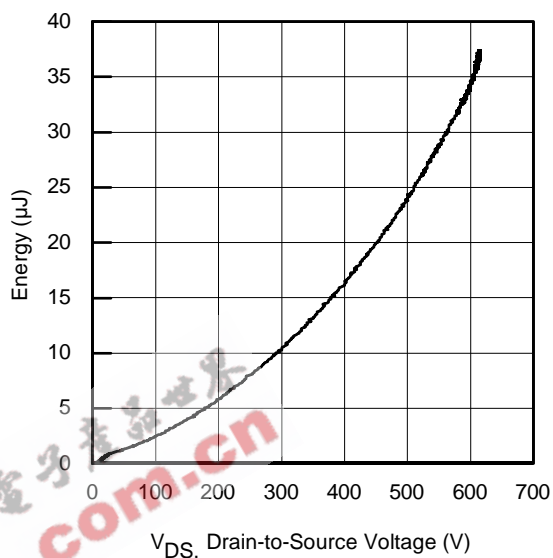


Fig 6. Typ. Output Capacitance Stored Energy vs. V_{DS}

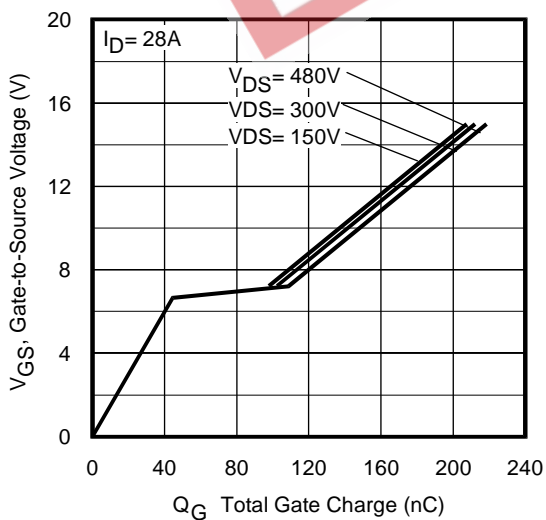


Fig 7. Typical Gate Charge vs. Gate-to-Source Voltage

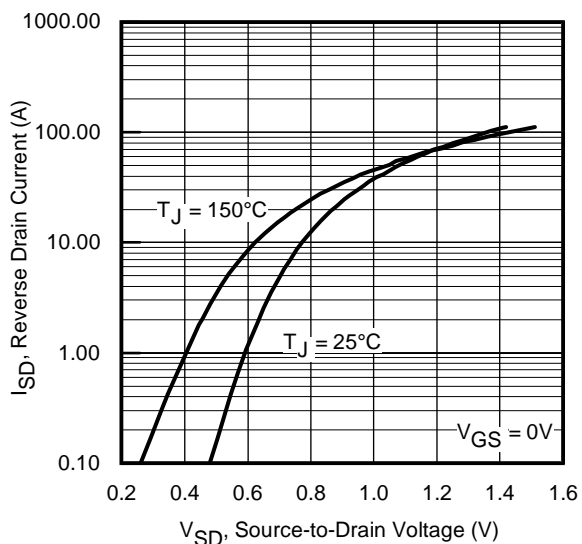


Fig 8. Typical Source-Drain Diode Forward Voltage

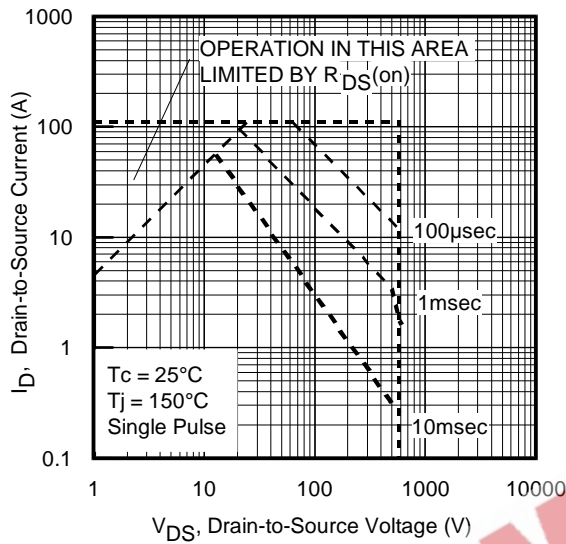


Fig 9. Maximum Safe Operating Area

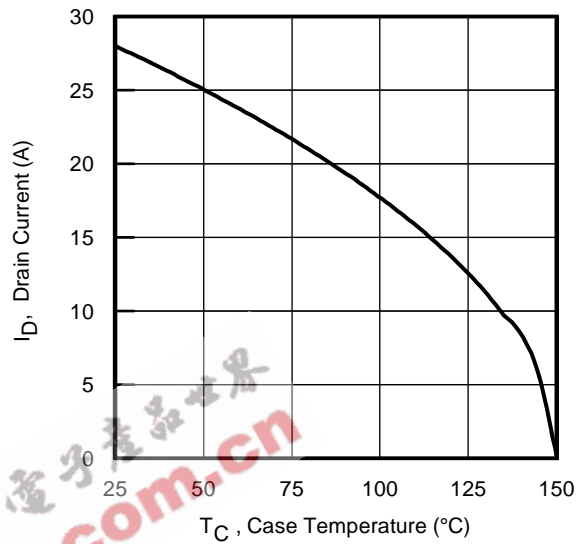


Fig 10. Maximum Drain Current vs. Case Temperature

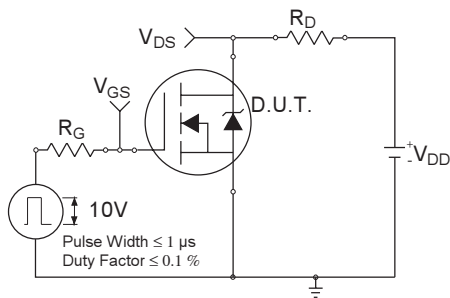


Fig 11a. Switching Time Test Circuit

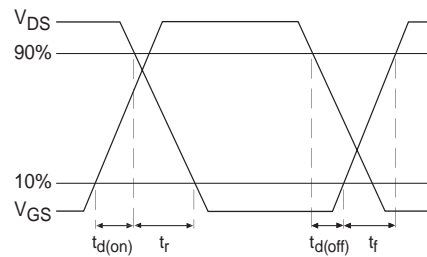


Fig 11b. Switching Time Waveforms

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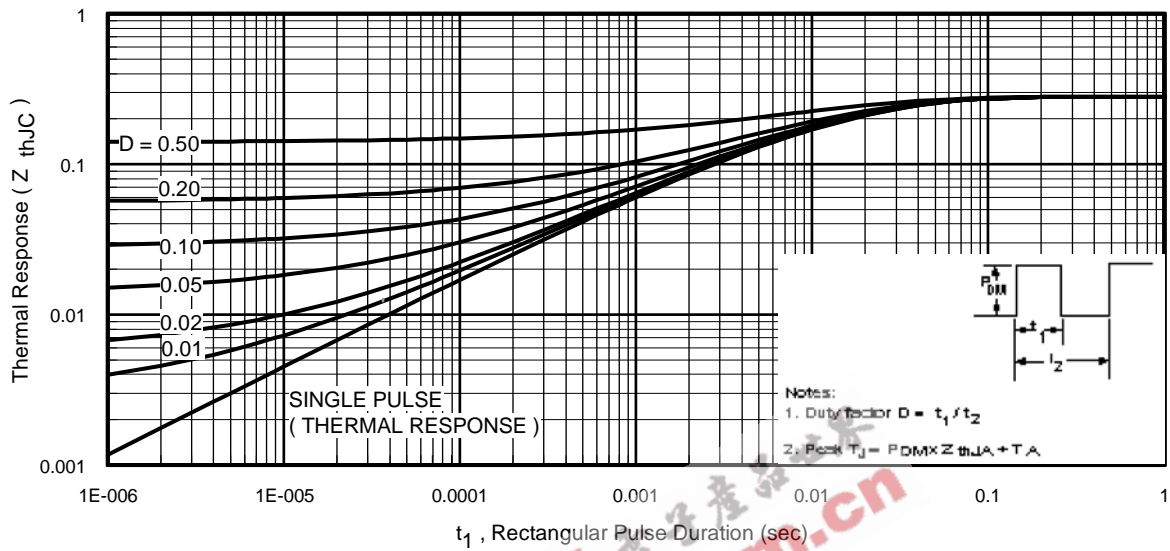


Fig 12. Maximum Effective Transient Thermal Impedance, Junction-to-Case

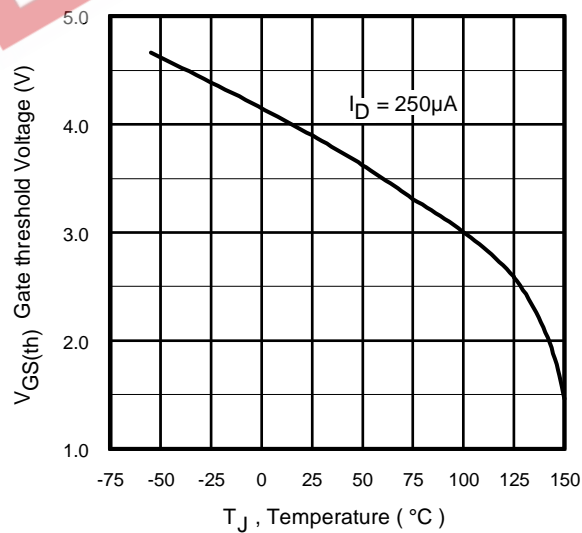


Fig 13. Threshold Voltage vs. Temperature

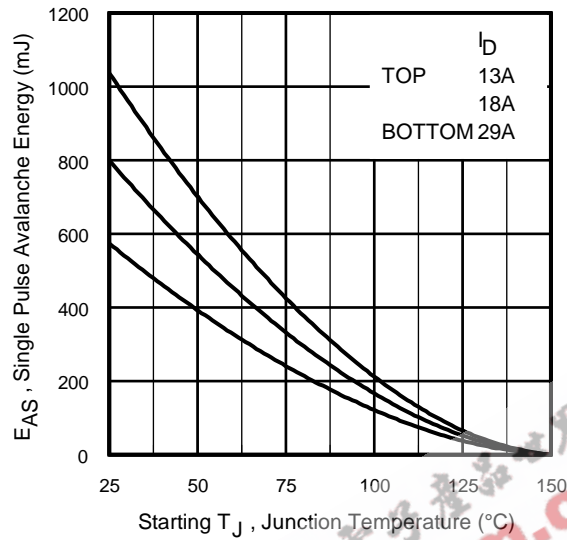


Fig 14a. Maximum Avalanche Energy vs. Drain Current

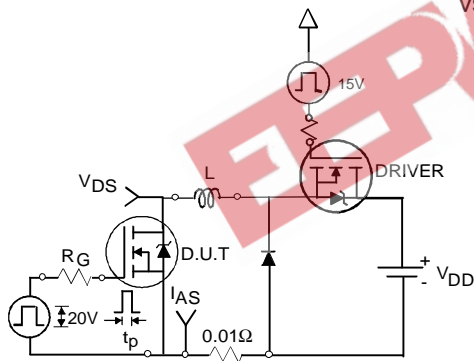


Fig 14b. Unclamped Inductive Test Circuit

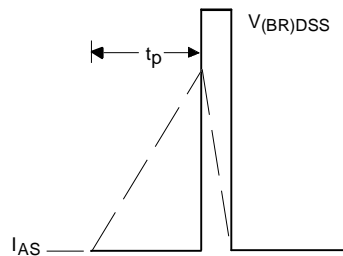


Fig 14c. Unclamped Inductive Waveforms

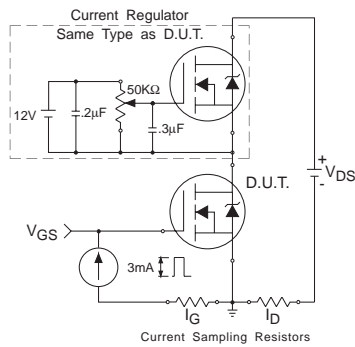


Fig 15a. Gate Charge Test Circuit

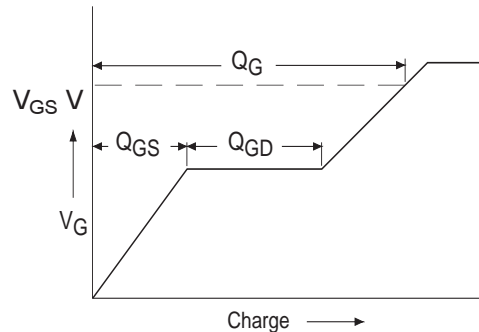
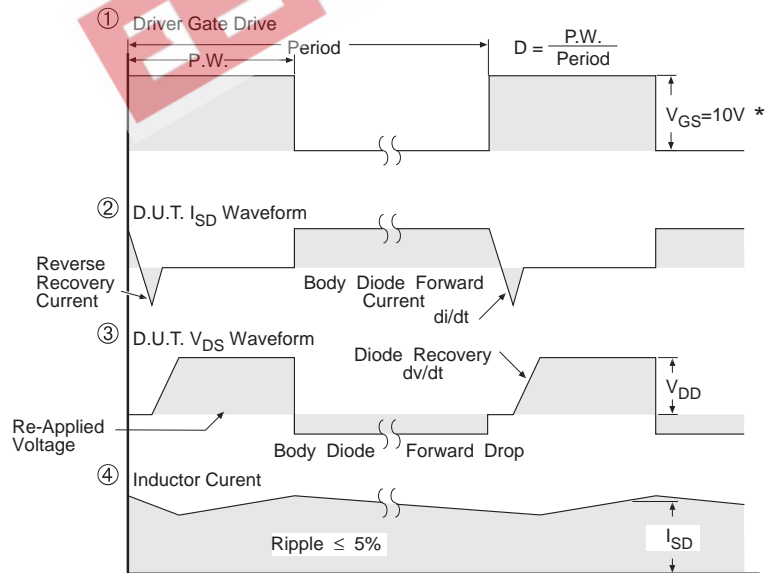
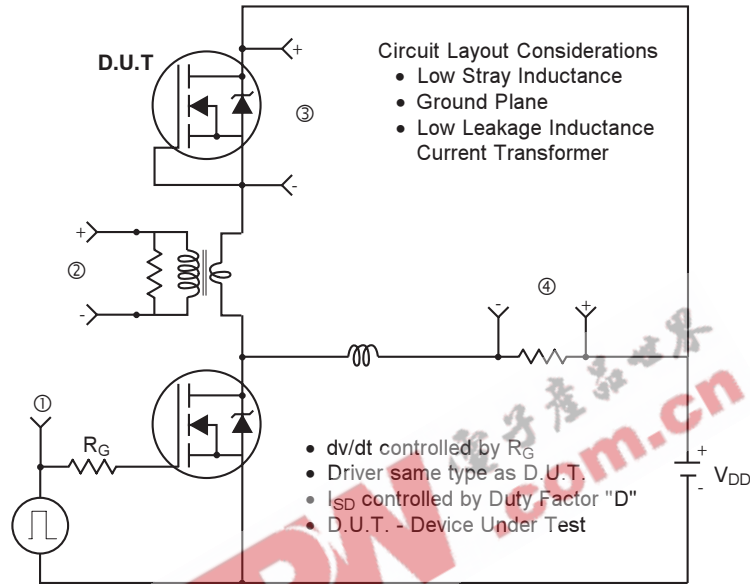


Fig 15b. Basic Gate Charge Waveform

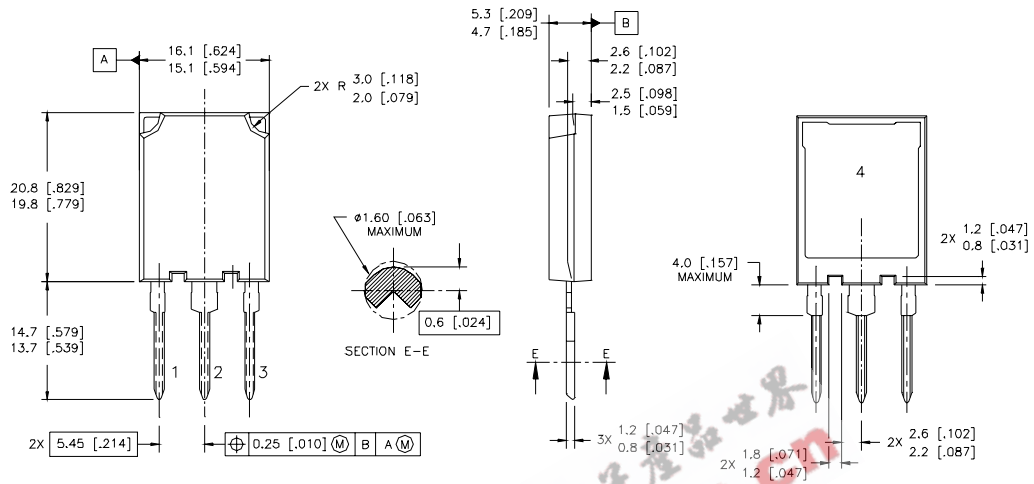
Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 16. For N-Channel HEXFET® Power MOSFETs

Case Outline and Dimensions — Super-247



NOTES:

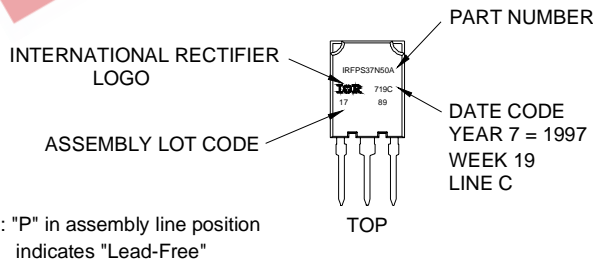
1. DIMENSIONS & TOLERANCING PER ASME Y14.5M-1994
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETRES [INCHES]

LEAD ASSIGNMENTS

MOSFET		IGBT	
1	- GATE	1	- GATE
2	- DRAIN	2	- COLLECTOR
3	- SOURCE	3	- EMITTER
4	- DRAIN	4	- COLLECTOR

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
 ASSEMBLY LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"



Super TO-247™ package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.